

# Jinyu Ni

## List of Publications by Year in descending order

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8  
papers

185  
citations

1683934

5  
h-index

1872570

6  
g-index

8  
all docs

8  
docs citations

8  
times ranked

318  
citing authors

#	ARTICLE	IF	CITATIONS
1	AlGaIn/GaN MOS-HEMT With $\text{HfO}_2$ Dielectric and $\text{Al}_2\text{O}_3$ Interfacial Passivation Layer Grown by Atomic Layer Deposition. IEEE Electron Device Letters, 2008, 29, 838-840.	2.2	125
2	The mobility of two-dimensional electron gas in AlGaIn/GaN heterostructures with varied Al content. Science in China Series F: Information Sciences, 2008, 51, 780-789.	1.1	26
3	Study of GaN MOS-HEMT using ultrathin $\text{Al}_2\text{O}_3$ dielectric grown by atomic layer deposition. Science in China Series D: Earth Sciences, 2009, 52, 2762-2766.	0.9	18
4	Effect of reactor pressure on the growth rate and structural properties of GaN films. Science Bulletin, 2009, 54, 2595-2598.	4.3	6
5	Development and characteristic analysis of enhancement-mode recessed-gate AlGaIn/GaN HEMT. Science in China Series D: Earth Sciences, 2008, 51, 784-789.	0.9	5
6	Improved electrical properties of the two-dimensional electron gas in AlGaIn/GaN heterostructures using high temperature AlN interlayers. Science China Technological Sciences, 2010, 53, 1567-1571.	2.0	4
7	Effect of high temperature AlN interlayer on the performance of AlGaIn/GaN properties. , 2009, , .		1
8	Improvement of electrical properties of AlGaIn/GaN heterostructures using multiple high-temperature AlN interlayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1934-1937.	0.8	0